0.00003% (typ)

0.00003% (typ)

 $2.7 \text{nV} / \sqrt{\text{Hz}}$  (typ)

±20V/µs (typ)

55MHz (typ)

140dB (typ)

ME49720 Dual High Performance, High Fidelity Audio Operational Amplifier

## LME49720 Dual High Performance, High Fidelity Audio Operational Amplifier

### **General Description**

N**ational** Semiconductor

The LME49720 is part of the ultra-low distortion, low noise, high slew rate operational amplifier series optimized and fully specified for high performance, high fidelity applications. Combining advanced leading-edge process technology with state-of-the-art circuit design, the LME49720 audio operational amplifiers deliver superior audio signal amplification for outstanding audio performance. The LME49720 combines extremely low voltage noise density ( $2.7nV/\sqrt{Hz}$ ) with vanishingly low THD+N (0.00003%) to easily satisfy the most demanding audio applications. To ensure that the most challenging loads are driven without compromise, the LME49720 has a high slew rate of  $\pm 20V/\mu$ s and an output current capability of  $\pm 26$ mA. Further, dynamic range is maximized by an output stage that drives  $2k\Omega$  loads to within 1V of either power supply voltage and to within 1.4V when driving  $600\Omega$  loads.

The LME49720's outstanding CMRR (120dB), PSRR (120dB), and  $V_{OS}$  (0.1mV) give the amplifier excellent operational amplifier DC performance.

The LME49720 has a wide supply range of  $\pm 2.5V$  to  $\pm 17V$ . Over this supply range the LME49720's input circuitry maintains excellent common-mode and power supply rejection, as well as maintaining its low input bias current. The LME49720 is unity gain stable. This Audio Operational Amplifier achieves outstanding AC performance while driving complex loads with values as high as 100pF.

The LME49720 is available in 8–lead narrow body SOIC, 8– lead Plastic DIP, and 8–lead Metal Can TO-99. Demonstration boards are available for each package.

### **Key Specifications**

Power Supply Voltage Range

±2.5V to ±17V

R <sub>L</sub> = 600Ω
Input Noise Density

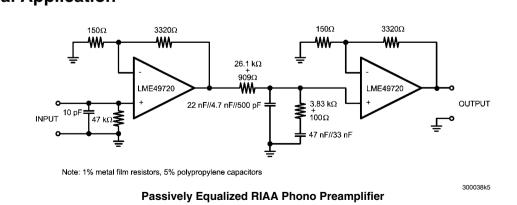
- Slew Bate
- Gain Bandwidth Product
- Open Loop Gain (R<sub>1</sub> = 600Ω)
- Input Bias Current
  10nA (typ)
- Input Offset Voltage 0.1mV (typ)
- DC Gain Linearity Error 0.000009%

### **Features**

- Easily drives 600Ω loads
- Optimized for superior audio signal fidelity
- Output short circuit protection
- PSRR and CMRR exceed 120dB (typ)
- SOIC, DIP, TO-99 metal can packages

### Applications

- Ultra high quality audio amplification
- High fidelity preamplifiers
- High fidelity multimedia
- State of the art phono pre amps
- High performance professional audio
- High fidelity equalization and crossover networks
- High performance line drivers
- High performance line receivers
- High fidelity active filters

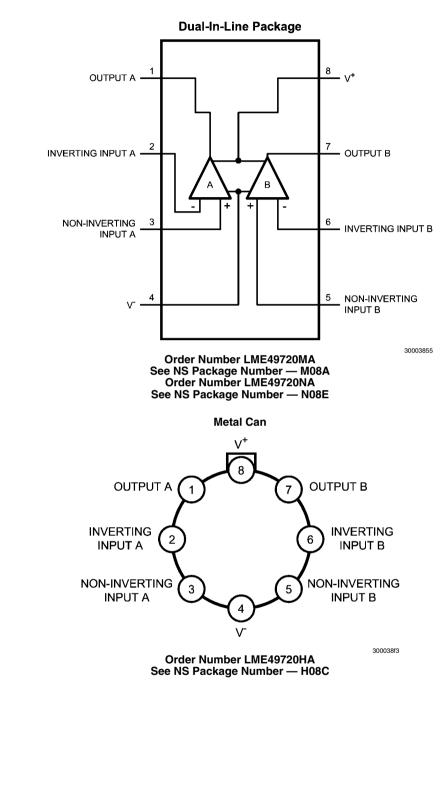


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- THD+N (A<sub>V</sub> = 1, V<sub>OUT</sub> =  $3V_{RMS}$ , f<sub>IN</sub> = 1kHz)

## Typical Application

### **Connection Diagrams**



Absolute	Maximum	Ratings	(Notes 1, 2)
----------	---------	---------	--------------

200V

100V

150°C

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/ Distributors for availability and specifications.

Distributors for availability a		Thermal Resistance		
Power Supply Voltage		θ <sub>JA</sub> (SO)	145°C/W	
$(V_{S} = V^{+} - V^{-})$	36V	θ <sub>JA</sub> (NA)	102°C/W	
Storage Temperature	–65°C to 150°C	θ <sub>JA</sub> (HA)	150°C/W	
Input Voltage	(V-) - 0.7V to (V+) + 0.7V	θ <sub>.IC</sub> (HA)	35°C/W	
Output Short Circuit (Note 3)	Continuous	Temperature Range		
Power Dissipation	Internally Limited	$T_{MIN} \le T_A \le T_{MAX}$	$-40^{\circ}C \le T_{\Delta} \le 85^{\circ}C$	
ESD Susceptibility (Note 4)	2000V	Supply Voltage Range	±2.5V ≤ V <sub>s</sub> ≤ ± 17V	
ESD Susceptibility (Note 5)			5	

Pins 1, 4, 7 and 8 Pins 2, 3, 5 and 6

Junction Temperature

## **Electrical Characteristics for the LME49720** (Notes 1, 2) The following specifications apply for $V_S = \pm 15V$ , $R_L = 2k\Omega$ , $f_{IN} = 1$ kHz, and $T_A = 25^{\circ}$ C, unless otherwise specified.

			LME49720		11
Symbol	Parameter	Conditions	Typical	Limit	Units
			(Note 6)	(Note 7)	– (Limits)
		$A_V = 1$ , $V_{OUT} = 3V_{rms}$			
THD+N	Total Harmonic Distortion + Noise	$R_{l} = 2k\Omega$	0.00003		% (max
		$R_{L} = 600\Omega$	0.00003	0.00009	
IMD	Intermodulation Distortion	$A_V = 1$ , $V_{OUT} = 3V_{RMS}$ Two-tone, 60Hz & 7kHz 4:1	0.00005		%
GBWP	Gain Bandwidth Product		55	45	MHz (mir
SR	Slew Rate		±20	±15	V/µs (mir
FPBW	Full Power Bandwidth	$V_{OUT} = 1V_{P-P}, -3dB$ referenced to output magnitude at f = 1kHz	10		MHz
t <sub>s</sub>	Settling time	$A_V = -1$ , 10V step, $C_L = 100pF$ 0.1% error range	1.2		μs
	Equivalent Input Noise Voltage	$f_{BW} = 20Hz$ to 20kHz	0.34	0.65	μV <sub>RMS</sub> (max)
e <sub>n</sub>	Equivalent Input Noise Density	f = 1kHz	2.7	4.7	nV/√H
		f = 10Hz	6.4		(max)
:	Current Naiss Density	f = 1kHz	1.6		A / 11
i <sub>n</sub>	Current Noise Density	f = 10Hz	3.1		p <b>A/</b> √H
V <sub>os</sub>	Offset Voltage		±0.1	±0.7	mV (max
Average Input Offset Voltage Drift vs		–40°C ≤ T <sub>A</sub> ≤ 85°C	0.2		μV/°C
PSRR Average Input Offset Voltage Shift vs Power Supply Voltage		$\Delta V_{S} = 20V$ (Note 8)	120	110	dB (min)
ISO <sub>CH-CH</sub>	Channel-to-Channel Isolation	f <sub>IN</sub> = 1kHz	118		dB
юо <sub>сн-сн</sub>		f <sub>IN</sub> = 20kHz	112		uD
I <sub>B</sub>	Input Bias Current	$V_{CM} = 0V$	10	72	nA (max
ΔI <sub>OS</sub> /ΔTemp Input Bias Current Drift vs Temperature		–40°C ≤ T <sub>A</sub> ≤ 85°C	0.1		nA/°C
l <sub>os</sub>	Input Offset Current	$V_{CM} = 0V$	11	65	nA (max
V <sub>IN-CM</sub>	Common-Mode Input Voltage Range		+14.1 -13.9	(V+) - 2.0 (V-) + 2.0	V (min)
CMRR	Common-Mode Rejection	-10V <vcm<10v< td=""><td>120</td><td>110</td><td>dB (min</td></vcm<10v<>	120	110	dB (min
7	Differential Input Impedance		30		kΩ
Z <sub>IN</sub>	Common Mode Input Impedance	-10V <vcm<10v< td=""><td>1000</td><td></td><td>MΩ</td></vcm<10v<>	1000		MΩ

			LME	LME49720	
Symbol	Parameter	Conditions	Typical	Limit	Units (Limits)
			(Note 6)	(Note 7)	
		$-10V$ <vout<10v, r<sub="">L = 600<math>\Omega</math></vout<10v,>	140	125	
A <sub>VOL</sub>	Open Loop Voltage Gain	-10V <vout<10v, <math="">R_L = 2k\Omega</vout<10v,>	140		dB (min)
		-10V <vout<10v, <math="">R_L = 10k\Omega</vout<10v,>	140		1
		R <sub>L</sub> = 600Ω	±13.6	±12.5	
V <sub>OUTMAX</sub>	Maximum Output Voltage Swing	$R_L = 2k\Omega$	±14.0		V (min)
		$R_L = 10k\Omega$	±14.1		1
I <sub>OUT</sub>	Output Current	R <sub>L</sub> = 600Ω, V <sub>S</sub> = ±17V	±26	±23	mA (min)
I <sub>OUT-CC</sub>	Instantaneous Short Circuit Current		+53 -42		mA
R <sub>OUT</sub>	Output Impedance	f <sub>IN</sub> = 10kHz Closed-Loop Open-Loop	0.01		Ω
C <sub>LOAD</sub>	Capacitive Load Drive Overshoot	100pF	16		%
I <sub>s</sub>	Total Quiescent Current	I <sub>OUT</sub> = 0mA	10	12	mA (max)

Note 1: Absolute Maximum Ratings indicate limits beyond which damage to the device may occur.

Note 2: Operating Ratings indicate conditions for which the device is functional, but do not guarantee specific performance limits. For guaranteed specifications and test conditions, see the Electrical Characteristics. The guaranteed specifications apply only for the test conditions listed. Some performance characteristics may degrade when the device is not operated under the listed test conditions.

Note 3: Amplifier output connected to GND, any number of amplifiers within a package.

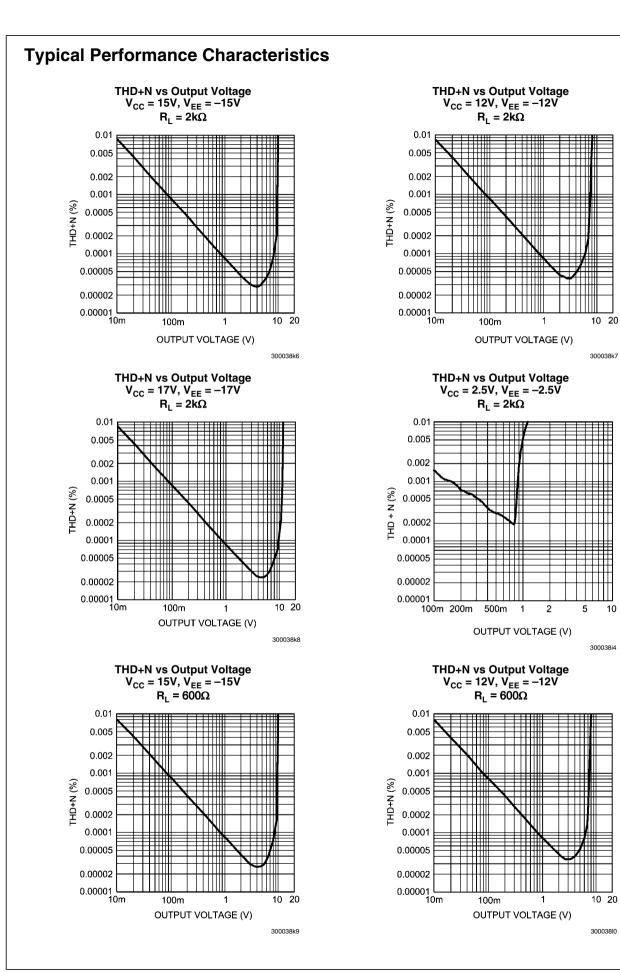
Note 4: Human body model, 100pF discharged through a 1.5k $\!\Omega$  resistor.

Note 5: Machine Model ESD test is covered by specification EIAJ IC-121-1981. A 200pF cap is charged to the specified voltage and then discharged directly into the IC with no external series resistor (resistance of discharge path must be under 50Ω).

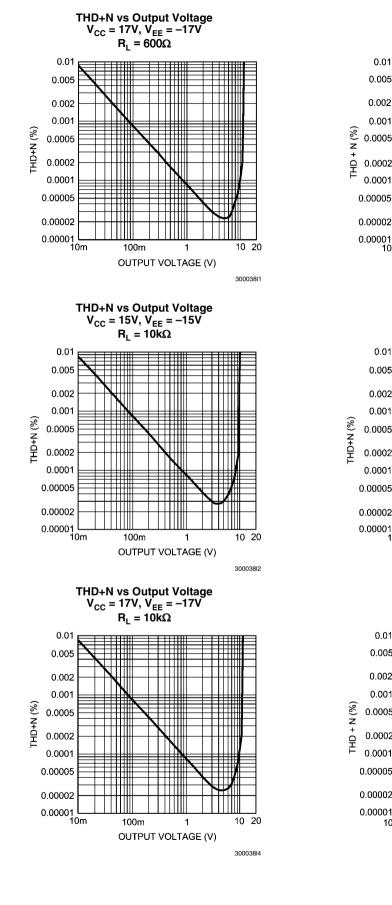
Note 6: Typical specifications are specified at +25°C and represent the most likely parametric norm.

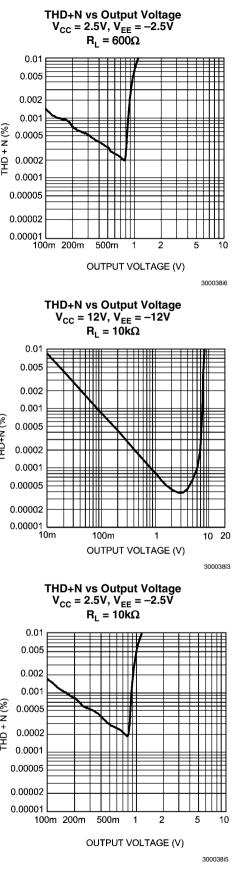
Note 7: Tested limits are guaranteed to National's AOQL (Average Outgoing Quality Level).

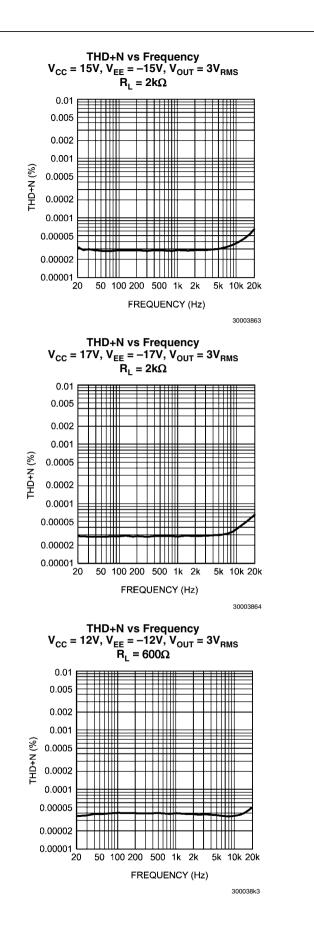
Note 8: PSRR is measured as follows:  $V_{OS}$  is measured at two supply voltages, ±5V and ±15V. PSRR = |  $20log(\Delta V_{OS}/\Delta V_S)$  |.

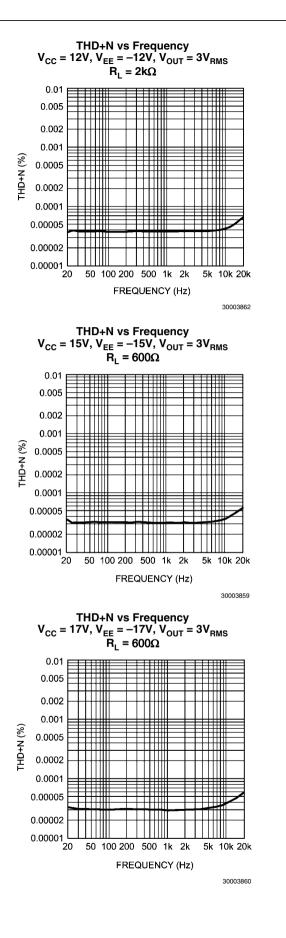


LME49720

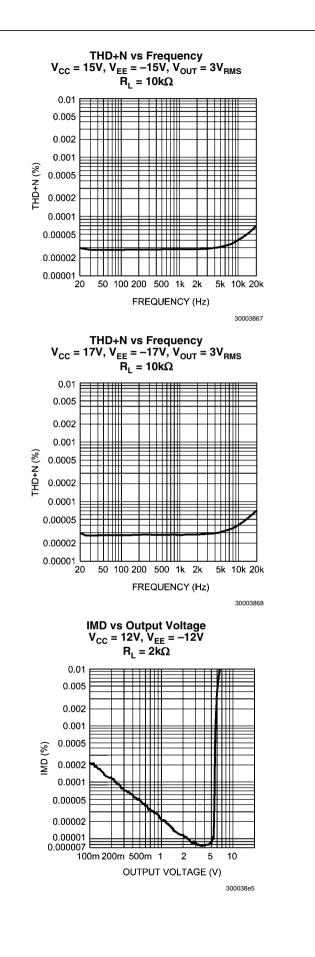


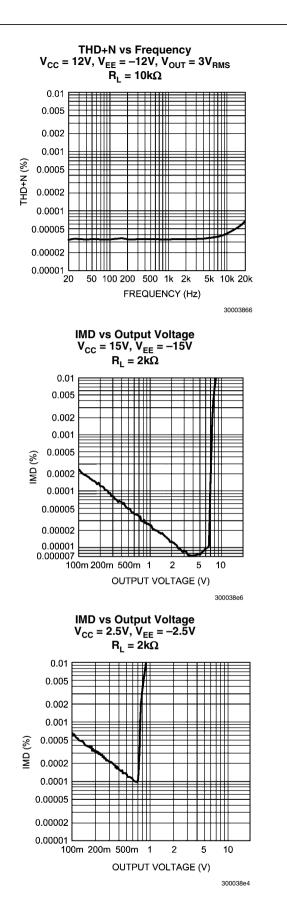




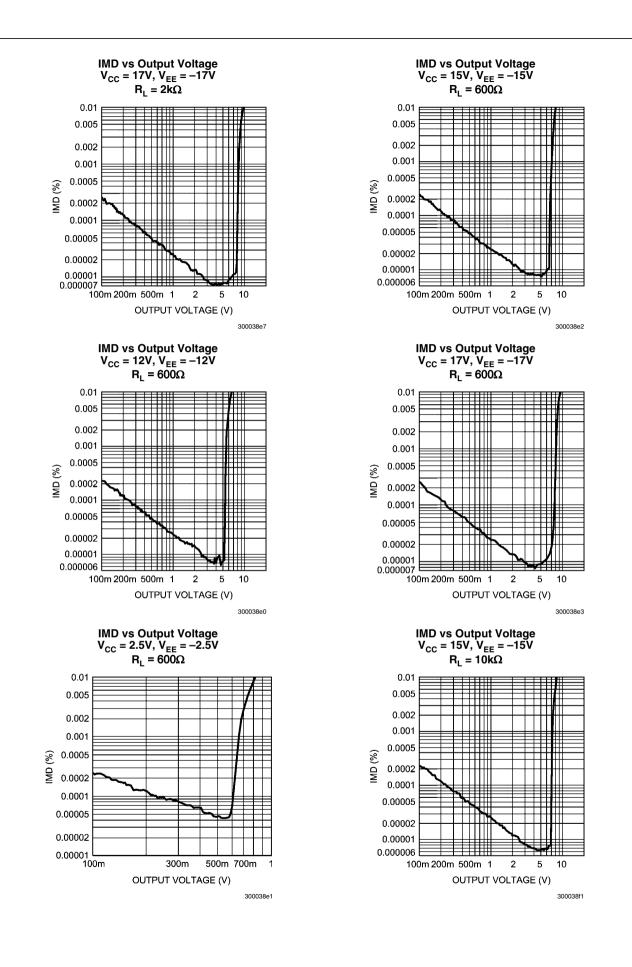




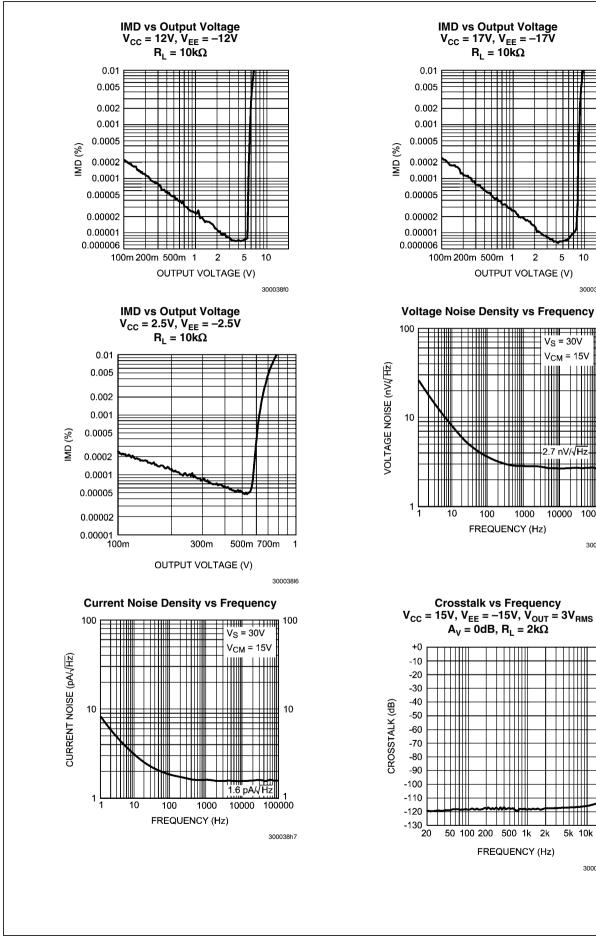












10 5

100 IIII

V<sub>S</sub> = 30V

1111

10000

2k

5k 10k 20k

300038c8

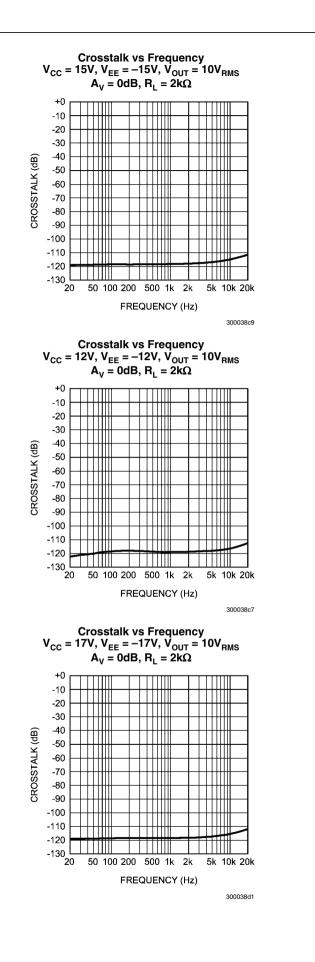
V<sub>CM</sub> = 15V

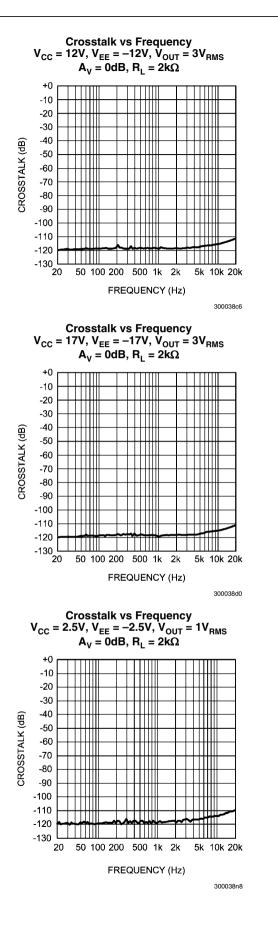
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10

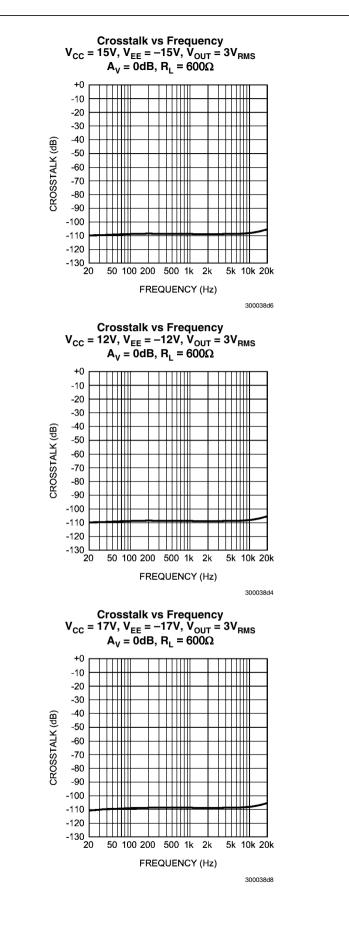
100000

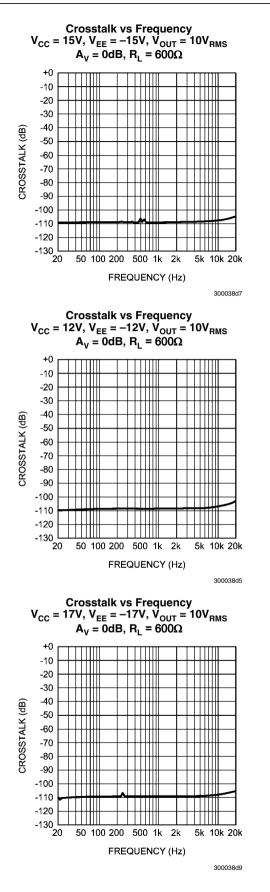
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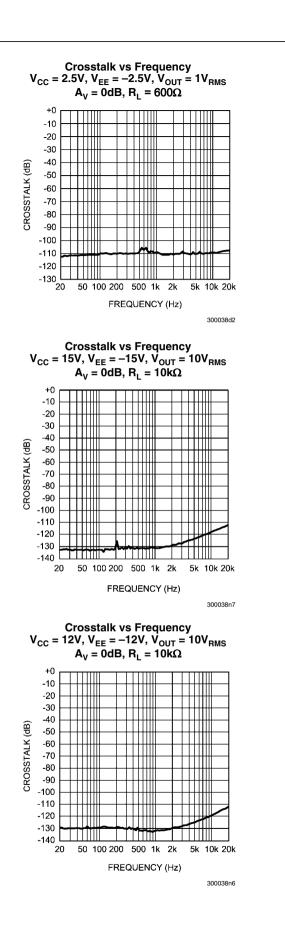


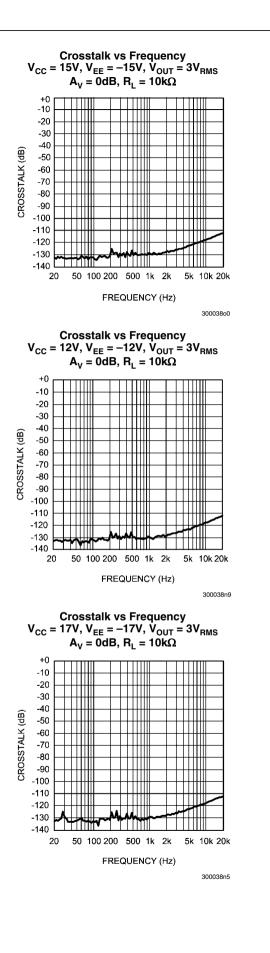


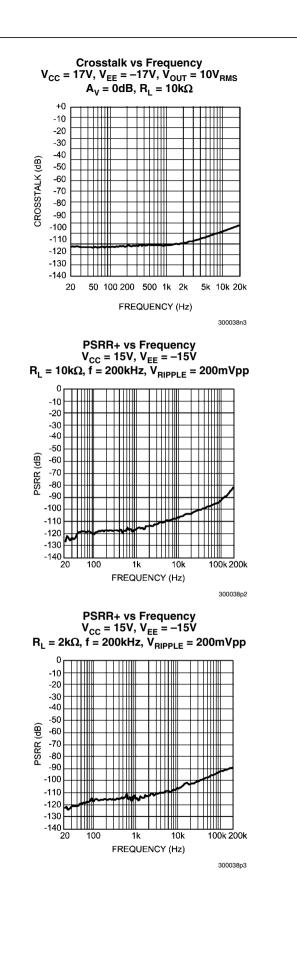


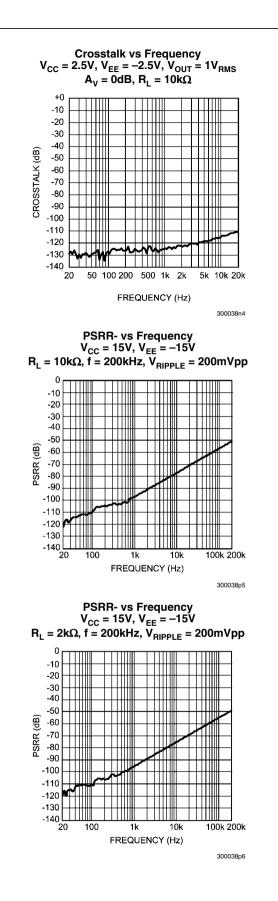


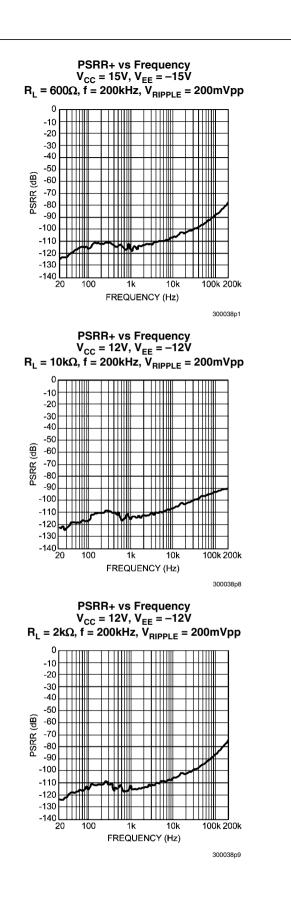


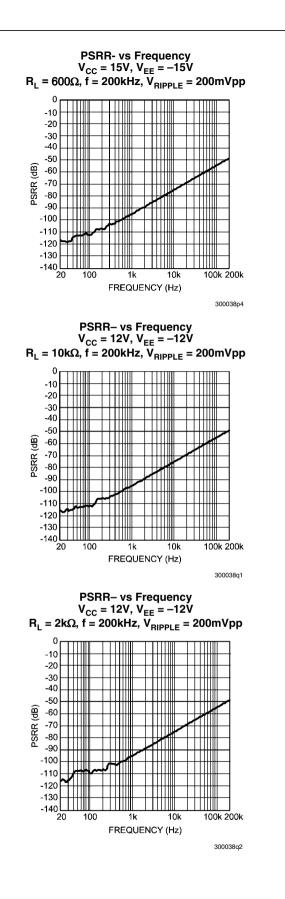


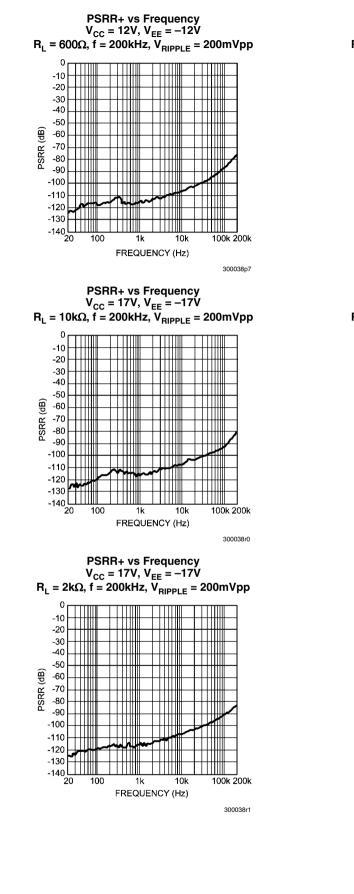


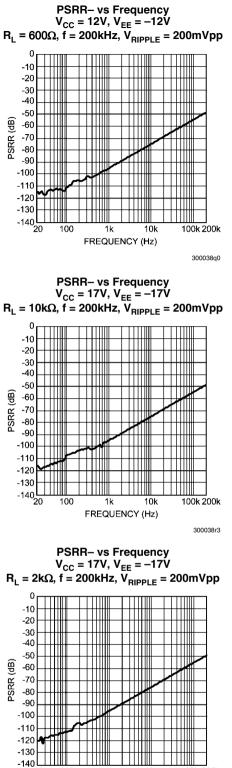












100

1k

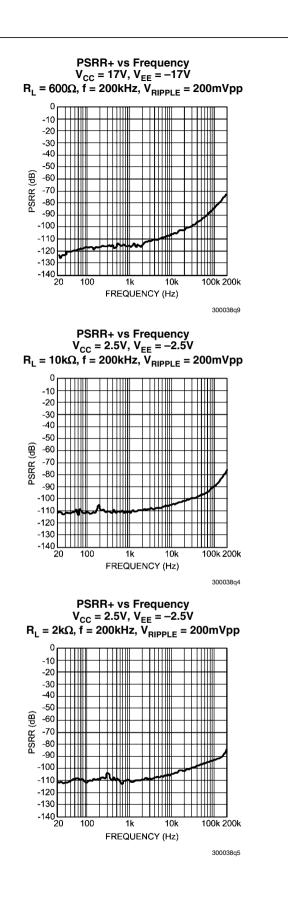
FREQUENCY (Hz)

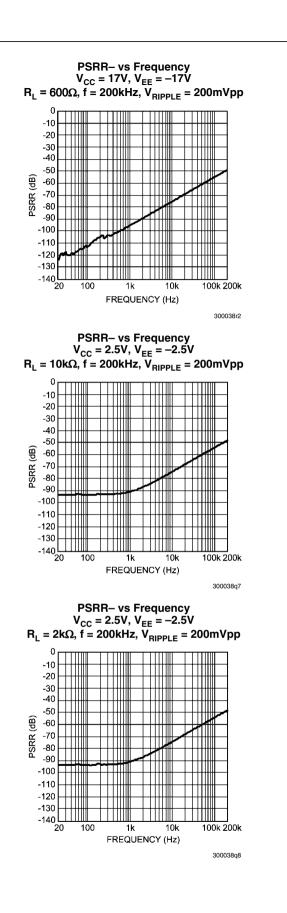
10k

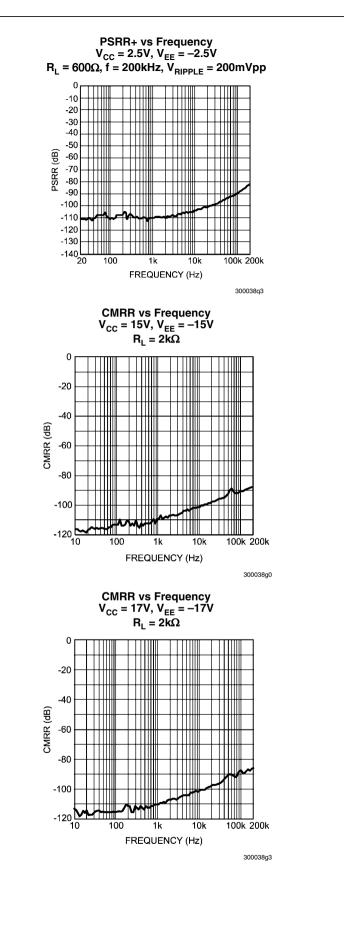
20

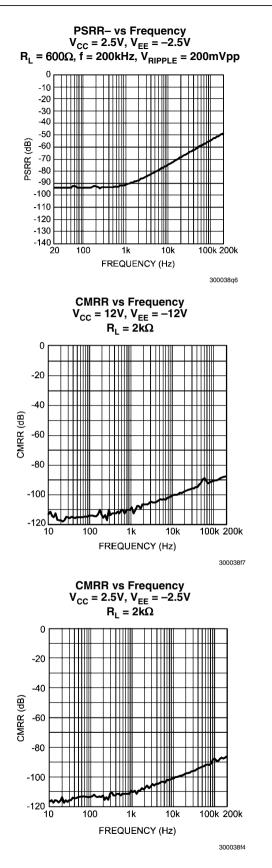
100k 200k

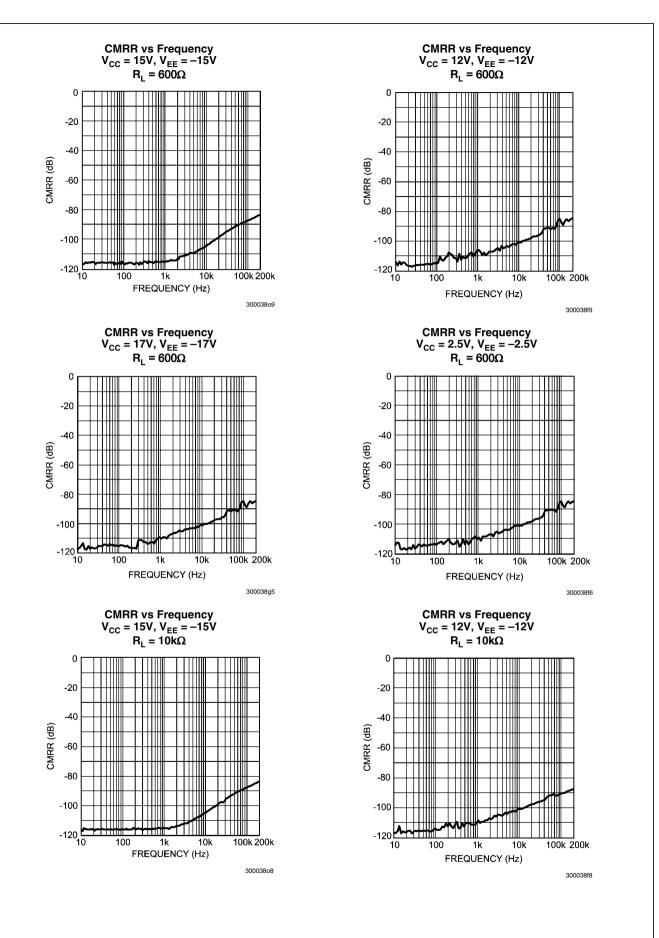
300038r4

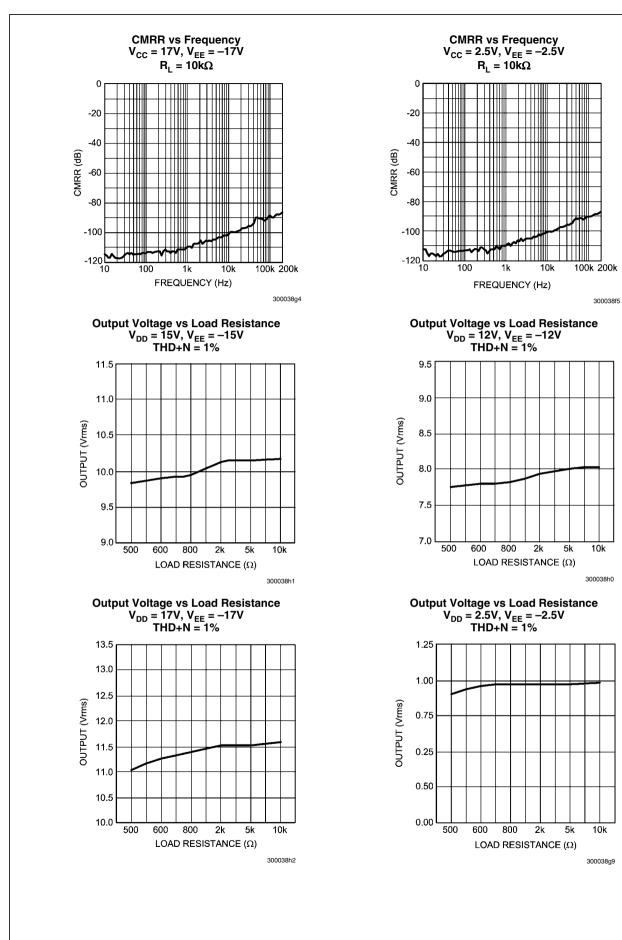




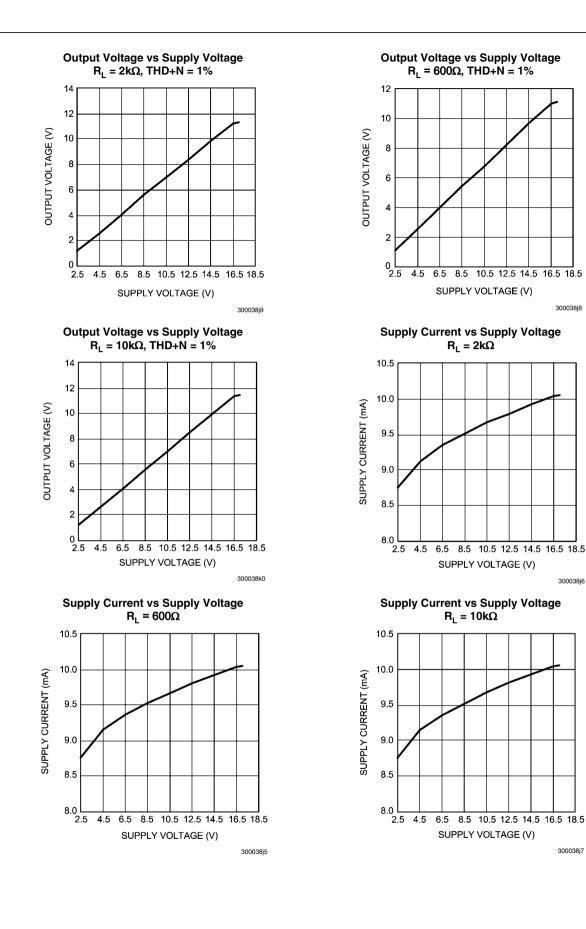




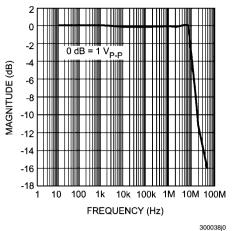


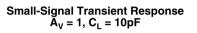


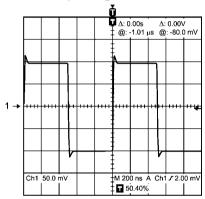




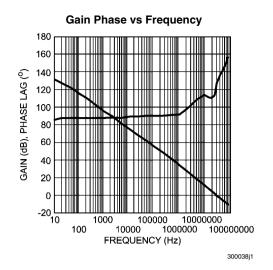
Full Power Bandwidth vs Frequency



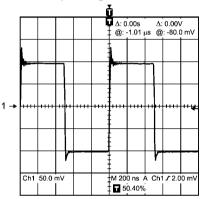








Small-Signal Transient Response  $A_V = 1, C_L = 100 pF$ 



300038i8

### **Application Information**

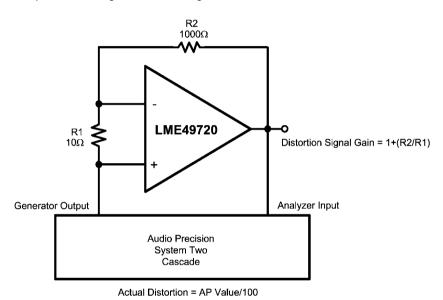
#### DISTORTION MEASUREMENTS

The vanishingly low residual distortion produced by LME49720 is below the capabilities of all commercially available equipment. This makes distortion measurements just slightly more difficult than simply connecting a distortion meter to the amplifier's inputs and outputs. The solution, however, is quite simple: an additional resistor. Adding this resistor extends the resolution of the distortion measurement equipment.

The LME49720's low residual distortion is an input referred internal error. As shown in Figure 1, adding the  $10\Omega$  resistor connected between the amplifier's inverting and non-inverting

inputs changes the amplifier's noise gain. The result is that the error signal (distortion) is amplified by a factor of 101. Although the amplifier's closed-loop gain is unaltered, the feedback available to correct distortion errors is reduced by 101, which means that measurement resolution increases by 101. To ensure minimum effects on distortion measurements, keep the value of R1 low as shown in Figure 1.

This technique is verified by duplicating the measurements with high closed loop gain and/or making the measurements at high frequencies. Doing so produces distortion components that are within the measurement equipment's capabilities. This datasheet's THD+N and IMD values were generated using the above described circuit connected to an Audio Precision System Two Cascade.



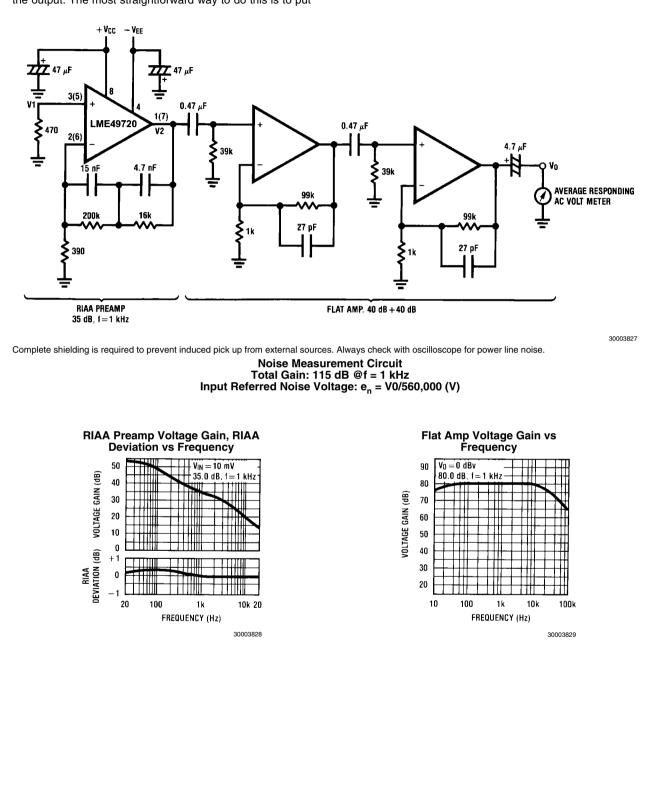
300038k4



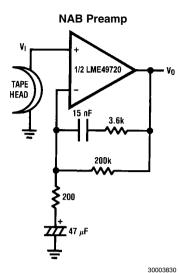
The LME49720 is a high speed op amp with excellent phase margin and stability. Capacitive loads up to 100pF will cause little change in the phase characteristics of the amplifiers and are therefore allowable.

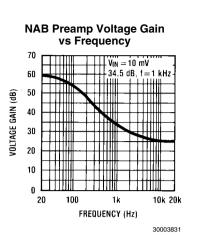
a resistor in series with the output. This resistor will also prevent excess power dissipation if the output is accidentally shorted.

Capacitive loads greater than 100pF must be isolated from the output. The most straightforward way to do this is to put



### TYPICAL APPLICATIONS



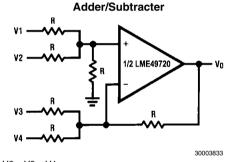


LME49720

 $A_V = 34.5$ F = 1 kHz E<sub>n</sub> = 0.38 µV A Weighted

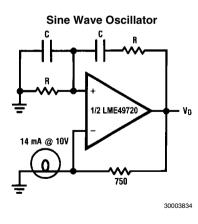
Balanced to Single Ended Converter

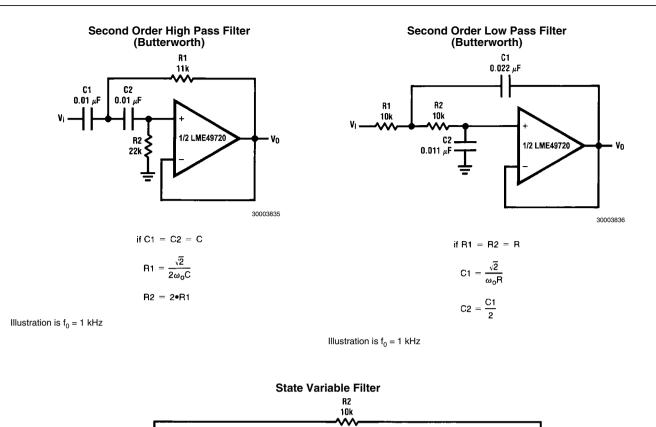
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 $V_0 = V1 + V2 - V3 - V4$ 

 $V_0 = V1 - V2$ 



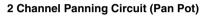


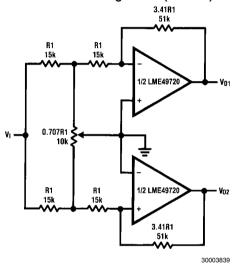
C1 0.01 μF C1 R2 R1 0.01 μF **R**1 16k 16k 10k 1/2 LME49720 R<sub>G</sub> 10k 1/2 LME49720 1/2 LME49720 VBP Инр VLP  $\sim$ 븣 R0 556 R2 10k ÷  $\sim$ 30003837

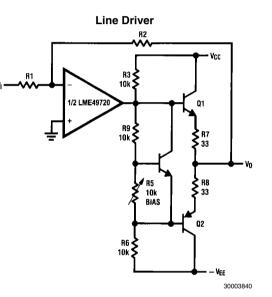
 $f_0 = \frac{1}{2\pi C1R1}, Q = \frac{1}{2}\left(1 + \frac{R2}{R0} + \frac{R2}{RG}\right), A_{BP} = QA_{LP} = QA_{LH} = \frac{R2}{RG}$ 

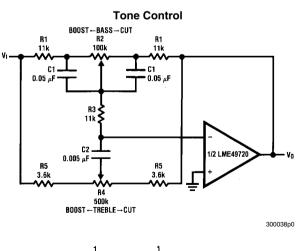
Illustration is  $f_0 = 1$  kHz, Q = 10, A<sub>BP</sub> = 1

**AC/DC Converter** C1 10 μF R5 20k Ś R3 10k R2 R4 20k 20k R1 7 D1 20k L 1S1588 Vin 1/2 LME49720 1/2 LME49720  $V_0 = |\overline{V_{IN}}|$ D2 181588 R6 15k ₹ R7 6.2k 30003838

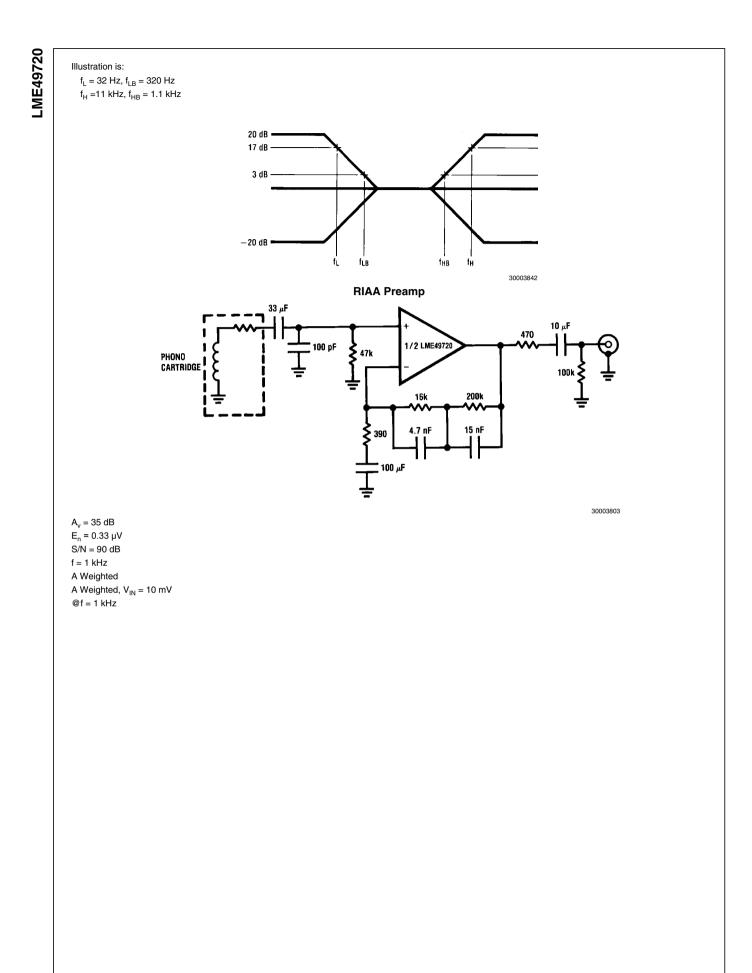


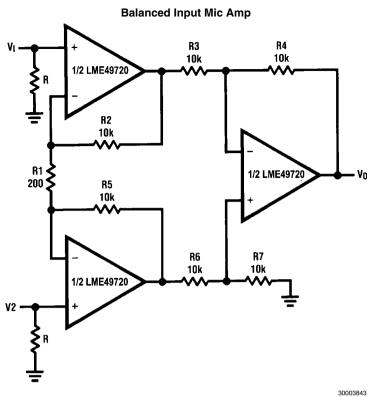






$$f_{L} = \frac{1}{2\pi R2C1}, f_{LB} = \frac{1}{2\pi R1C1}$$
$$f_{H} = \frac{1}{2\pi R5C2}, f_{HB} = \frac{1}{2\pi (R1 + R5 + 2R3)C2}$$





300030

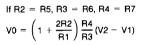
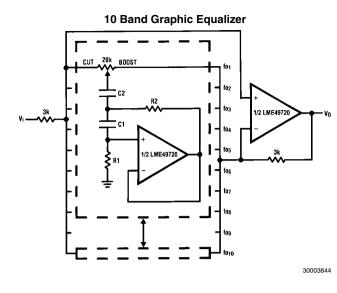


Illustration is: V0 = 101(V2 - V1)



fo (Hz)	<b>C</b> <sub>1</sub>	C <sub>2</sub>	R <sub>1</sub>	R <sub>2</sub>
32	0.12µF	4.7µF	75kΩ	500Ω
64	0.056µF	3.3µF	68kΩ	510Ω
125	0.033µF	1.5µF	62kΩ	510Ω
250	0.015µF	0.82µF	68kΩ	470Ω
500	8200pF	0.39µF	62kΩ	470Ω
1k	3900pF	0.22µF	68kΩ	470Ω
2k	2000pF	0.1µF	68kΩ	470Ω
4k	1100pF	0.056µF	62kΩ	470Ω
8k	510pF	0.022µF	68kΩ	510Ω
16k	330pF	0.012µF	51kΩ	510Ω

Note 9: At volume of change =  $\pm 12 \text{ dB}$ 

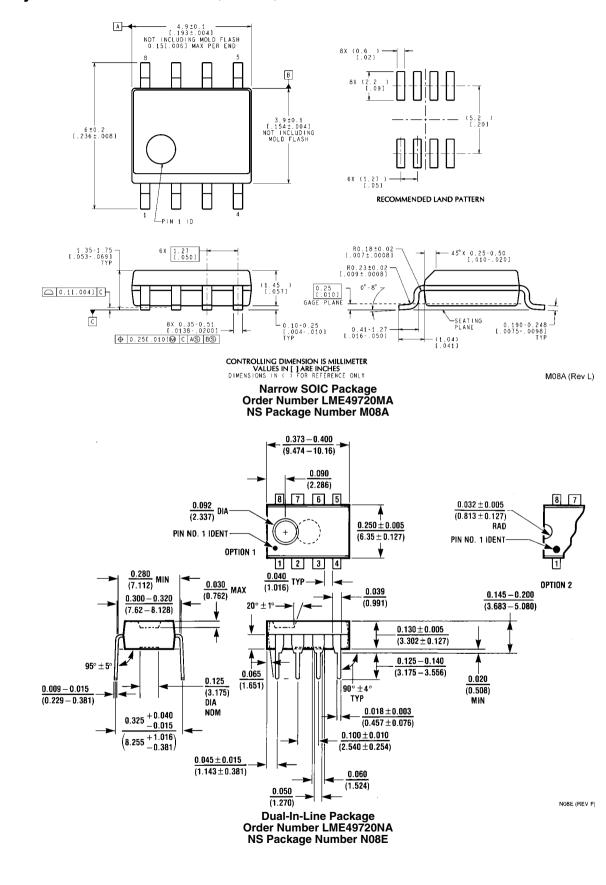
Q = 1.7

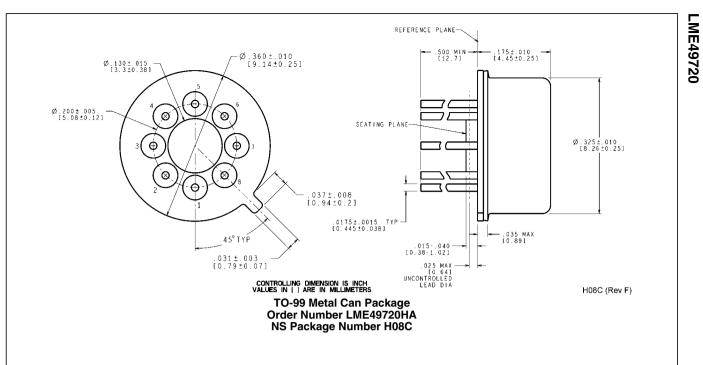
Reference: "AUDIO/RADIO HANDBOOK", National Semiconductor, 1980, Page 2-61

## **Revision History**

Rev	Date	Description
1.0	03/30/07	Initial release.
1.1	05/03/07	Put the "general note" under the EC table.
1.2	10/22/07	Replaced all the PSRR curves.

### Physical Dimensions inches (millimeters) unless otherwise noted





## Notes

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